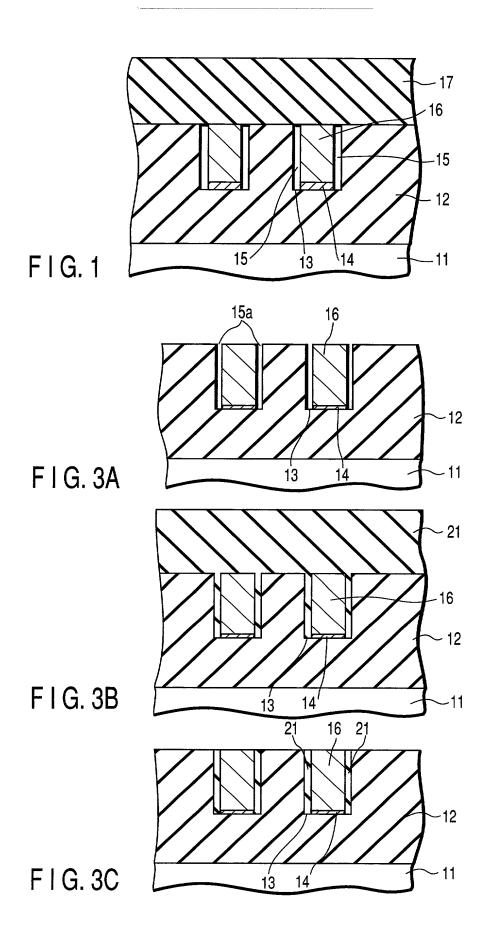
Inventor: Hiroyuki NITTA, et al.

Entitled: "Semiconductor Device Having a Wiring Layer of Damascene Structure and Method for Manufacturing the Same" Client*Matter: 01701.00086

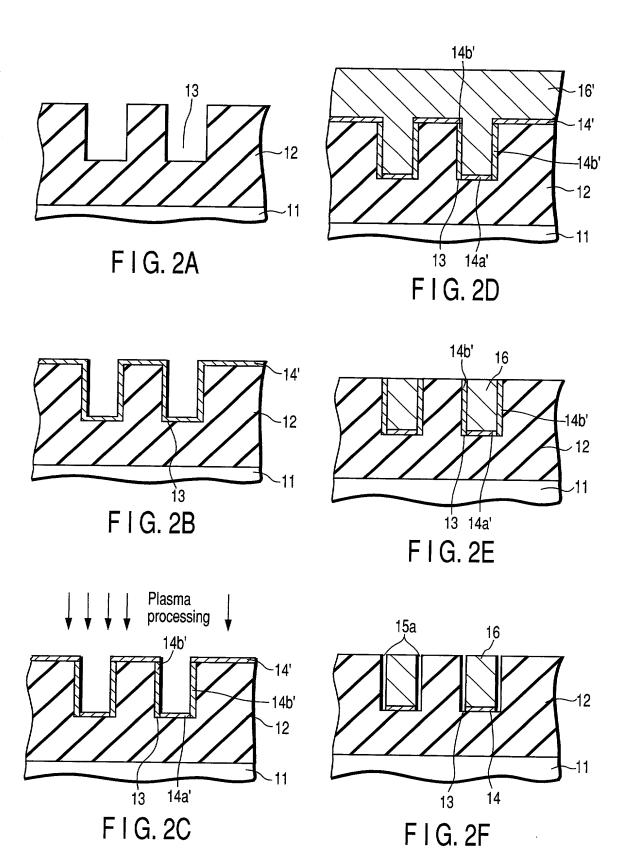
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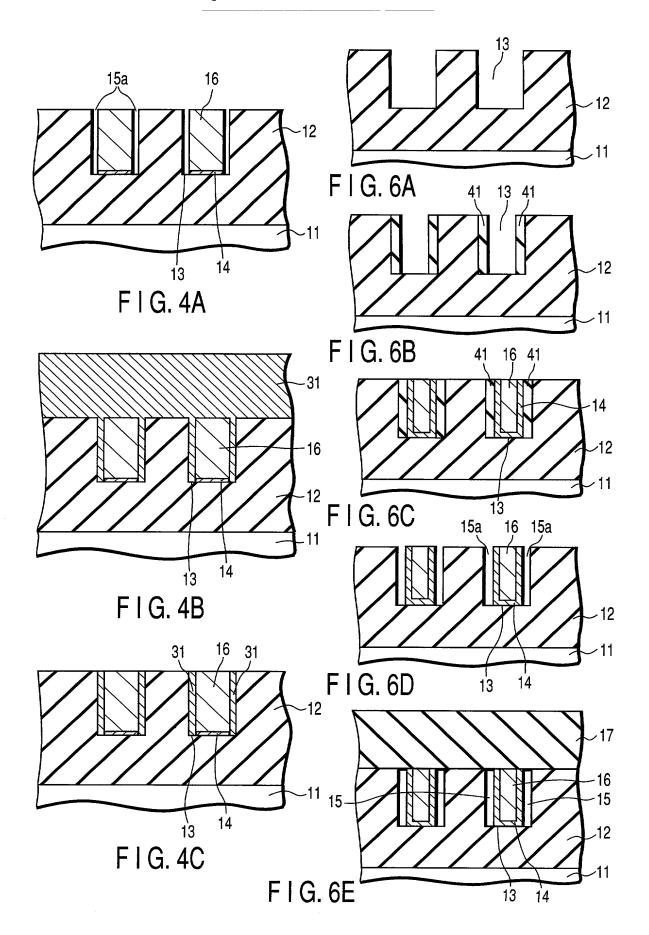


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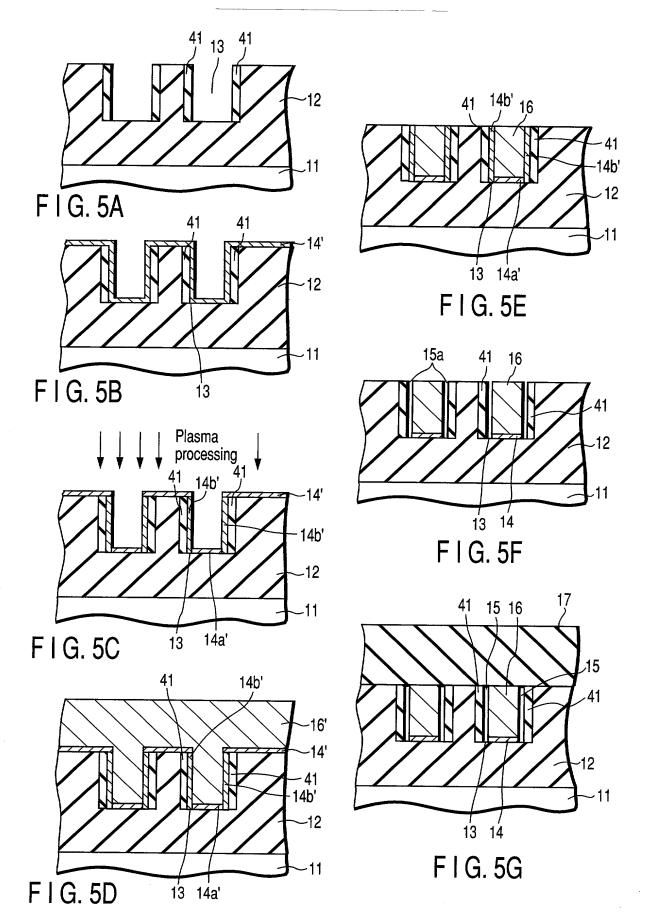
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Inventor: Hiroyuki NITTA, et al.
Entitled: "Semiconductor Device Having a
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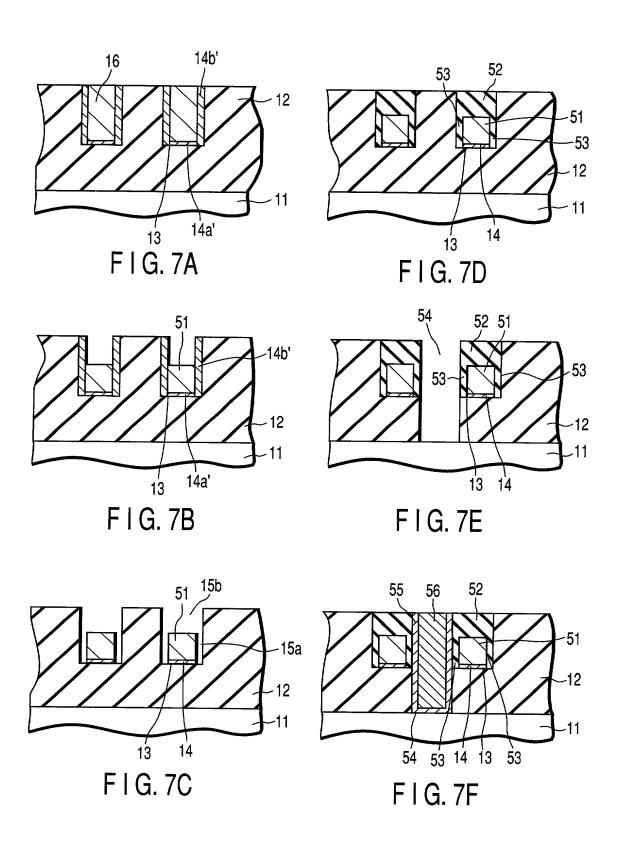
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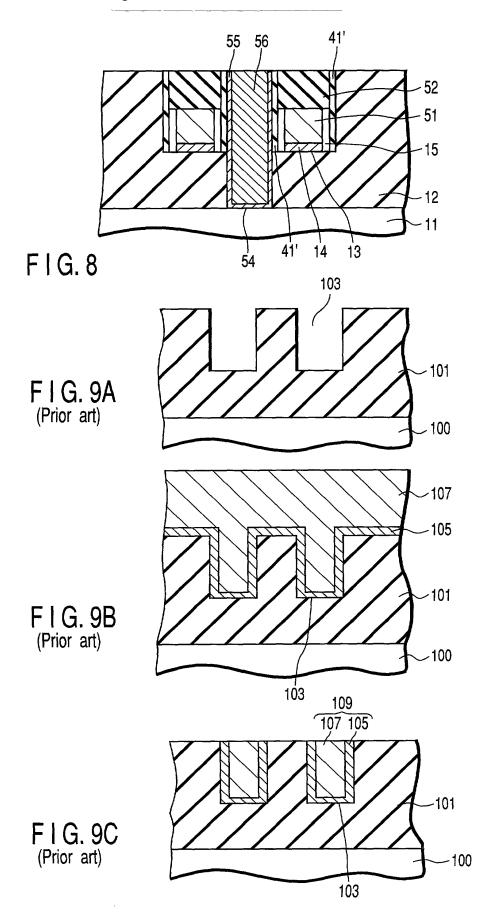
Inventor: Hiroyuki NITTA, et al. Entitled: "Semiconductor Device Having a Wiring Layer of Damascene Structure and Method for Manufacturing the Same" Client*Matter: 01701.00086

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Inventor: Hiroyuki NITTA, et al.
Entitled: "Semiconductor Device Having a
Wiring Layer of Damascene Structure and
Method for Manufacturing the Same"
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Inventor: Hiroyuki NITTA, et al. Entitled: "Semiconductor Device Having a Wiring Layer of Damascene Structure and Method for Manufacturing the Same"

Client*Matter: 01701.00086

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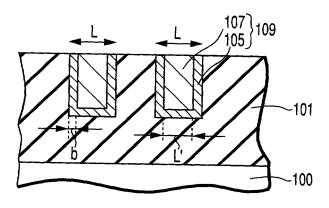


FIG. 10A (Prior art)

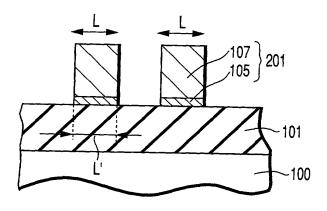


FIG. 10B (Prior art)